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INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)		APPLICANTS Takamitsu HIGUCHI et al.					
		FILING DATE August 21, 2003					
		U.S. PATENT DOCUMENTS					
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME		CLASS	SUB CLASS
DV	1	6,232,242 B1	05/15/2001	Hata et al.			
	2	5,155,658	10/13/1992	Inam et al.			
	3	5,173,474	12/22/1992	Connell et al.			
	4	5,270,298	12/14/1993	Ramesh			
	5	5,358,925	10/25/1994	Neville Connell et al.			
	6	5,416,062	05/16/1995	Harada et al.			
	7	5,801,105	09/01/1998	Yano et al.			
	8	5,810,923	09/22/1998	Yano et al.			
	9	5,828,080	10/27/1998	Yano et al.			
	10	6,045,626	04/04/2000	Yano et al.			
	11	6,096,434	08/01/2000	Yano et al.			
DV	12	6,121,647	09/19/2000	Yano et al.			
FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY		CLASS	SUB CLASS
DV	13	JP A 2000-332569 (with abstract and translation)	11/30/2000	Japan			
	14	JP A 2001-077102 (with abstract and translation)	03/23/2001	Japan			
	15	JP A 6-097452 (with abstract and translation)	04/08/1994	Japan			
	16	JP A 8-109099 (with abstract and translation)	04/30/1996	Japan			
	17	JP A 8-255790 (with abstract and translation)	10/01/1996	Japan			
	18	JP A 8-264524 (with abstract and translation)	10/11/1996	Japan			
	19	JP A 9-110592 (with abstract and translation)	04/28/1997	Japan			
DV	20	JP A 10-017394 (with abstract and translation)	01/20/1998	Japan			
EXAMINER	<i>Shuland</i>				DATE CONSIDERED <i>12/18/04</i>		
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D✓	21	JP A 9-263494 (with abstract and translation)	10/07/1997	Japan	
	22	JP A 10-107216 (with abstract and translation)	04/24/1998	Japan	
	23	JP A 11-026296 (with abstract and translation)	01/29/1999	Japan	
	24	JP A 2000-101345 (with abstract and translation)	04/07/2000	Japan	
	25	JP A 2002-009358 (with abstract and translation)	01/11/2002	Japan	
	26	JP A 2001-122698 (with abstract and translation)	05/08/2001	Japan	
D✓	27	JP A 10-265948 (with abstract and translation)	10/06/1998	Japan	

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)

D✓	28	Fork et al., "Epitaxial yttria-stabilized zirconia on hydrogen-terminated Si by pulsed laser deposition", Appl. Phys. Letter 57, September 10, 1990, pp 1137-1139
D✓	29	Haakenaasen et al., "High quality crystalline YBa ₂ Cu ₃ O _{7-δ} films on thin silicon substrates", Appl. Phys. Lett. 64, March 21, 1994, pp 1573-1575
D✓	30	Hou et al., "Structure and properties of epitaxial Ba _{0.5} Sr _{0.5} TiO _y /SrRuO ₃ /ZrO ₂ heterostructure on Si grown by off-axis sputtering", Appl. Phys. Lett. 67, September 4, 1005, pp 1387-1389

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